

LMBTA92LT1G

S-LMBTA92LT1G

High Voltage Transistor PNP Silicon

1. FEATURES

- High voltage.
- For Telephony or Professional communication equipment applications.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBTA92LT1G	2D	3000/Tape&Reel
LMBTA92LT3G	2D	10000/Tape&Reel

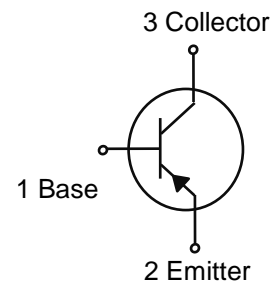
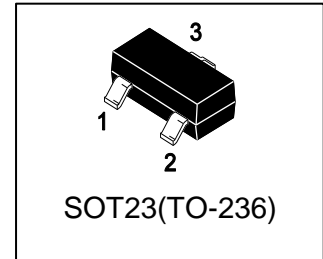
3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-300	V
Collector–Base Voltage	VCBO	-300	V
Emitter–Base Voltage	VEBO	-5	V
Collector Current — Continuous	IC	-500	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	556	°C/W
Junction and Storage temperature	TJ, Tstg	-55~+150	°C

1. FR-5 = 1.0×0.75×0.062 in.

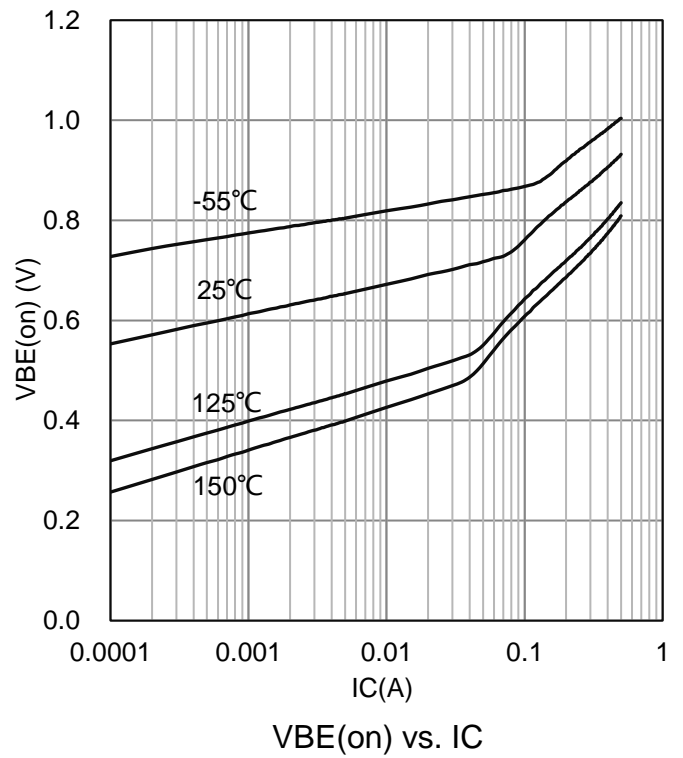
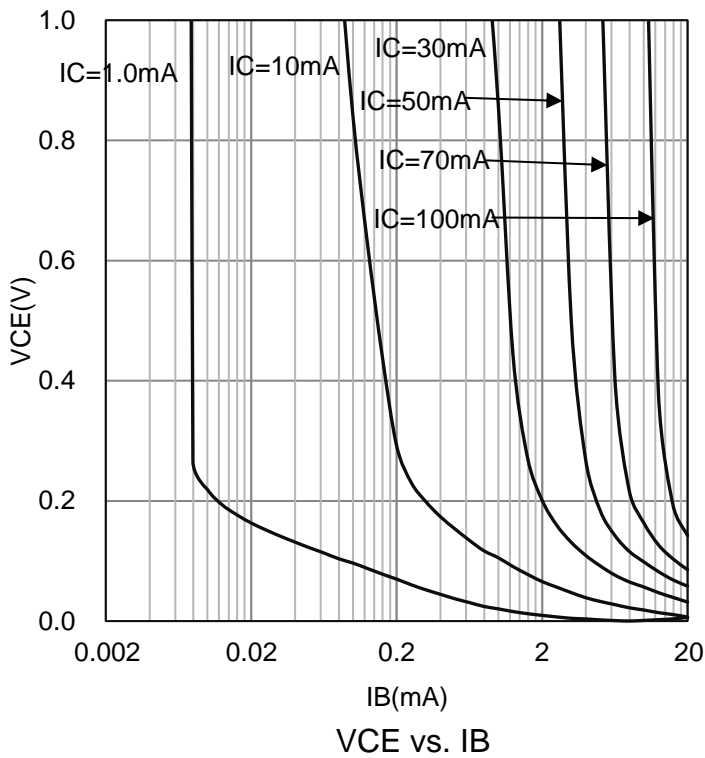
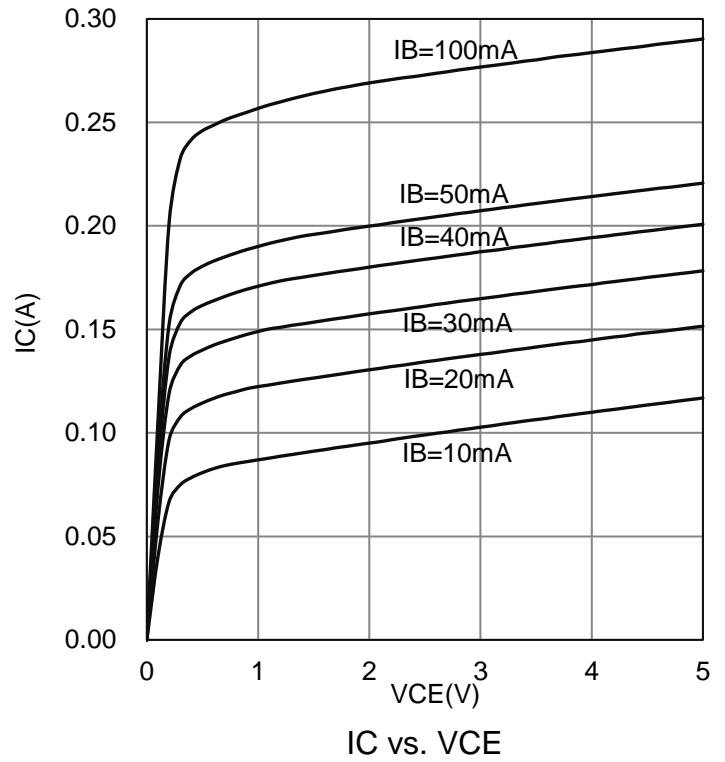
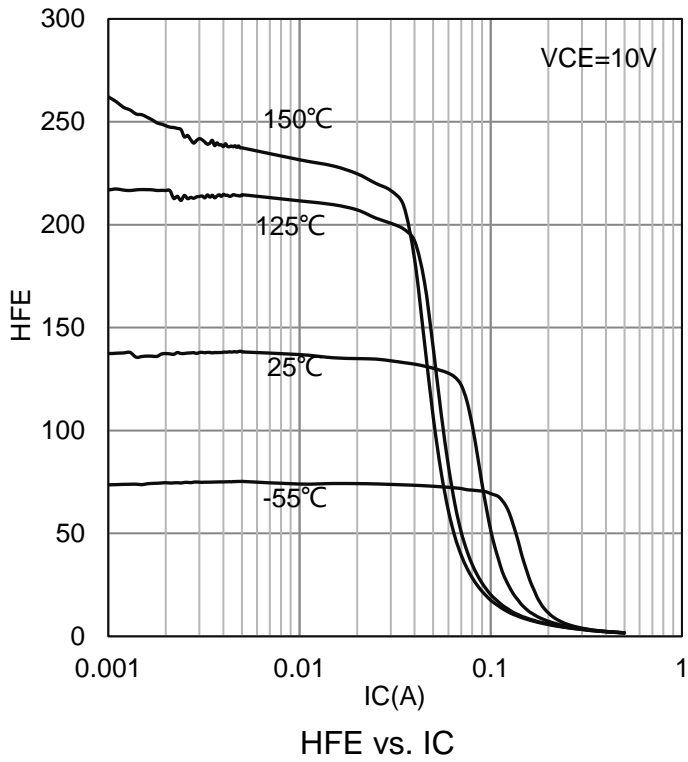


5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

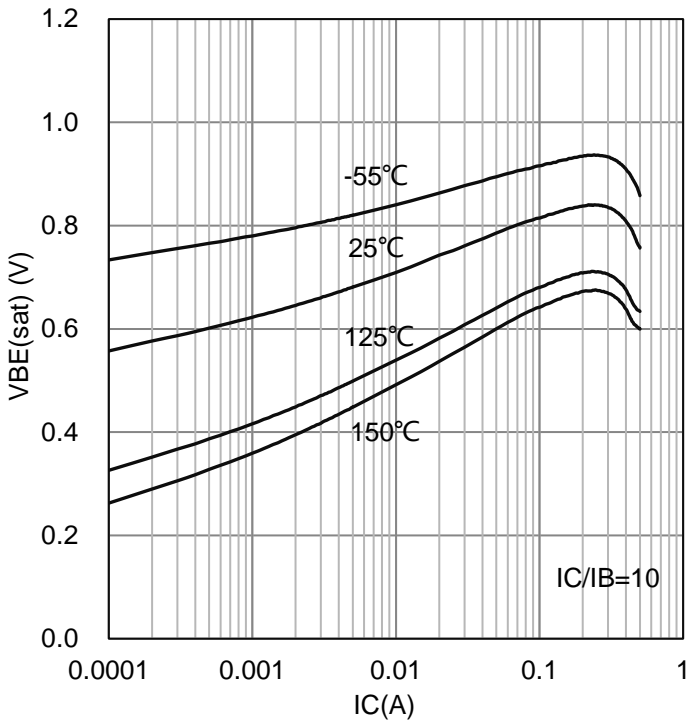
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage(Note 2) (IC = -1 mA, IB = 0)	VBR(CEO)	-300	-	-	V
Collector–Emitter Breakdown Voltage (IC = -100 μA, IE = 0)	V(BR)CBO	-300	-	-	V
Emitter–Base Breakdown Voltage (IE = -100 μA, IC = 0)	VBR(EBO)	-5	-	-	V
Collector-Base Cutoff Current (VCB = -200V, IE = 0)	ICBO	-	-	-100	nA
Emitter-Base Cutoff Current (VEB = -6.0V, IC = 0)	IEBO	-	-	-100	nA
Collector-Emitter Cutoff Current (VCE = -300 V, IB = 0)	ICEO	-	-	-10	μA
DC Current Gain (VCE=-10V,IC=-1mA) (VCE=-10V,IC=-10mA) (VCE=-10V,IC=-30mA)	HFE	25 40 25	- - -	- - -	
Collector–Emitter Saturation Voltage (IC=-20mA,IB=-2mA)	VCE(sat)	-	-	-0.5	V
Base–Emitter Saturation Voltage (IC=-20mA,IB=-2mA)	VBE(sat)	-	-	-0.9	V
Current–Gain — Bandwidth Product (IC = -10mA, VCE = -20V, f = 100MHz)	fT	50	-	-	MHz
Collector – Base Capacitance (VCB = -20 V, IE = 0, f = 1.0 MHz)	Ccb	-	-	6	pF

2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

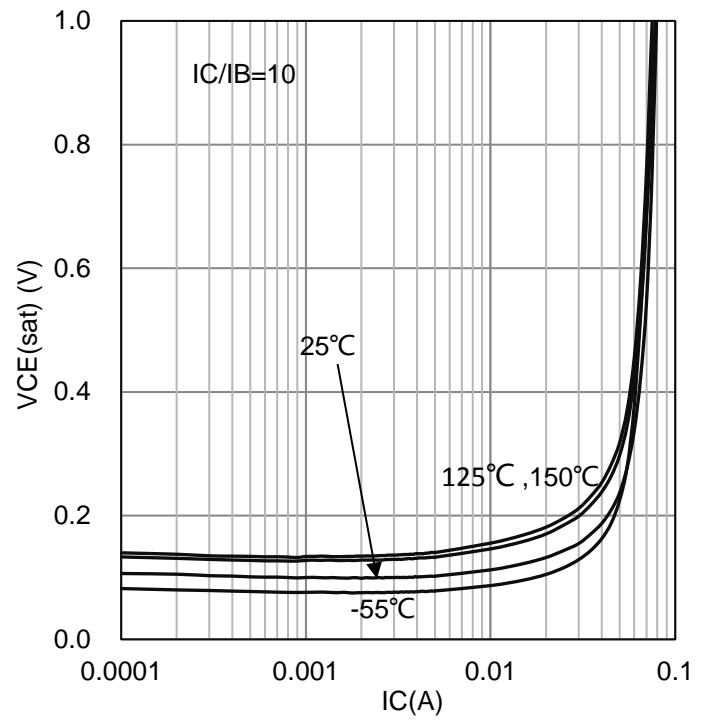
6.ELECTRICAL CHARACTERISTICS CURVES



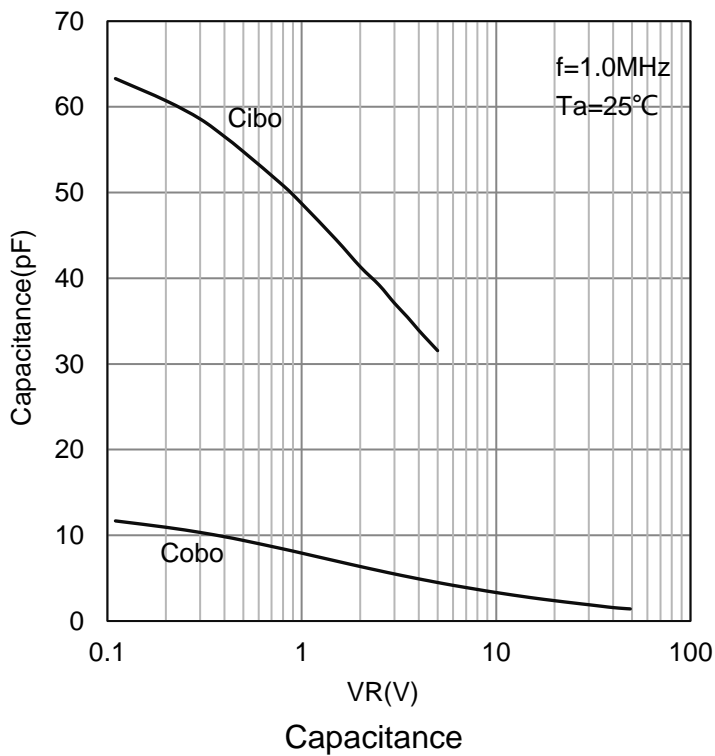
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



VBE(sat) vs. IC

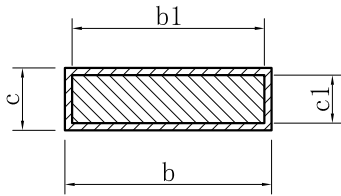
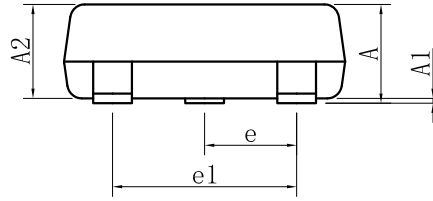
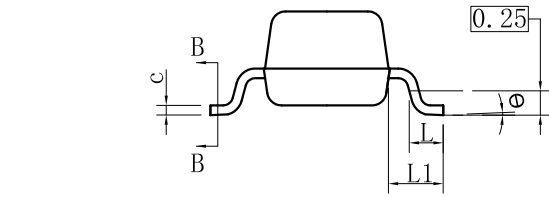


VCE(sat) vs. IC

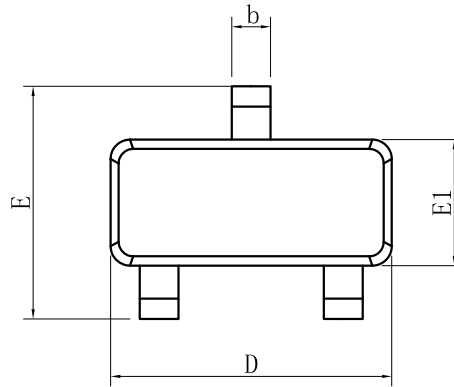


Capacitance

7. OUTLINE AND DIMENSIONS



SECTION B-B

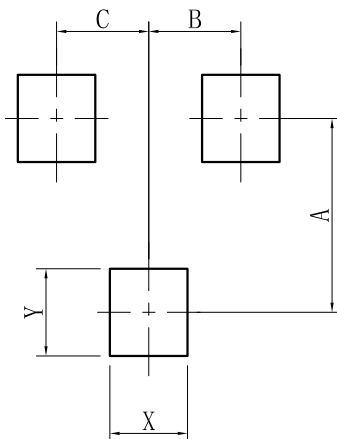


SOT23			
DIM	MIN	NOR	MAX
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.50
b1	0.30	0.40	0.45
c	0.08	-	0.20
c1	0.08	0.10	0.16
D	2.80	2.90	3.04
E	2.10	-	2.64
E1	1.20	1.30	1.40
e	0.95BSC		
e1	1.90BSC		
L	0.40	0.46	0.60
L1	0.54REF		
θ	0°	-	8°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um

8. SOLDERING FOOTPRINT



SOT-23	
DIM	(mm)
X	0.80
Y	0.90
A	2.00
B	0.95
C	0.95

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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